

Silicon NPN Power Transistors

2SC4075

DESCRIPTION

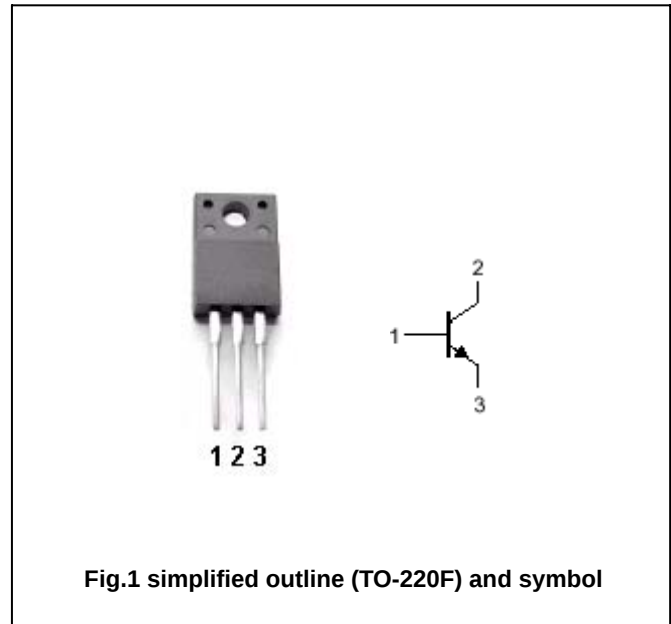
- With TO-220F package
- High voltage
- Wide area of safe operation

APPLICATIONS

- Color TV chroma output ,sound output and B/W TV video output ,audio output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.2	A
I_{CM}	Collector current-peak		0.7	A
P_C	Collector power dissipation	$T_a=25^{\circ}\text{C}$	2	W
		$T_C=25^{\circ}\text{C}$	10	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

Silicon NPN Power Transistors**2SC4075****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; I _B =0	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10 μ A; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10 μ A; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA; I _B =5m A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			0.1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	μ A
h _{FE}	DC current gain	I _C =10mA ; V _{CE} =10V	40		200	
f _T	Transition frequency	I _C =10mA ; V _{CE} =30V	50			MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =50V; f=1MHz			5.3	pF

◆ **h_{FE} Classifications**

C	D	E
40-80	60-120	100-200

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PACKAGE OUTLINE

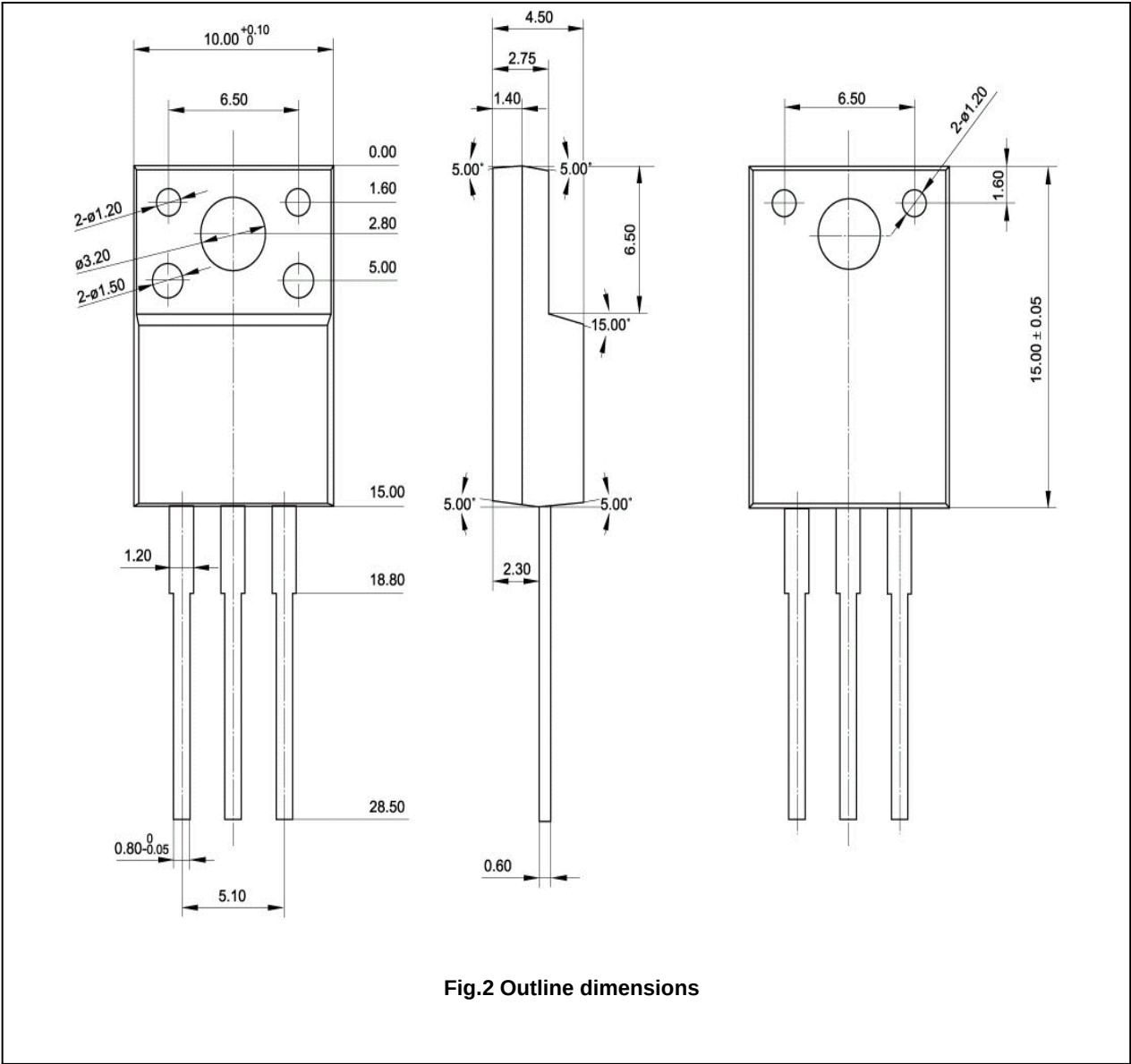


Fig.2 Outline dimensions